Amendments to the Specification:

Please replace the first paragraph, beginning at page 1, after the title, with the following amended paragraph:

CROSS-REFERENCE TO RELATED APPLICATIONS

This application is a continuation application of (and claims the benefit of priority under 35 U.S.C. 120) to U.S. Application Serial No. 09/876,258, filed on June 6, 2001, which claims priority to Provisional U.S. Patent Application Serial No. 60/210,258, filed June 7, 2000, all of which are incorporated herein by reference.

Please replace the paragraph beginning at page 4, line 28 with the following amended paragraph:

Good mixing performance in each operating band can be achieved by biasing the FETs 12a and 12b so that, for operation in the first band, the RF1_IN signal flows only through the first FET 12a and for operation in the second band, the RF2_IN signal flows only through the second FET 12b. In other words, the second FET 12b is turned "off" when the local oscillator signal LO1 is applied to the gate 18a of the first FET 12a, whereas the first FET [12b] 12a is turned "off" when the local oscillator signal LO2 is applied to the gate 18b of the second FET 12b. Consequently, there is virtually no signal degradation as compared to a single band mixer.

Please replace the paragraph beginning at page 5, line 5 with the following amended paragraph:

The FETs 12a and 12b can be turned off by providing the proper DC voltages to the gates 18a and 18b, respectively. In the illustrated implementation, when the first local input signal LO1 is applied to the first FET 12a, a negative voltage is generated at the gate 18b of the second FET 12b, thereby turning off the second FET 12b. Similarly, when the second local input signal LO2 is applied to the second FET 12b, a negative voltage is generated at the gate 18a of the first FET 12a, thereby turning off the [second] first FET 12a.